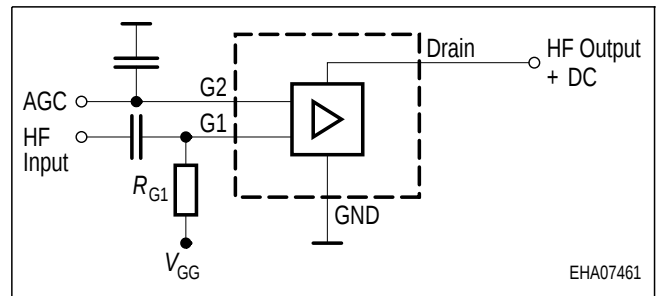
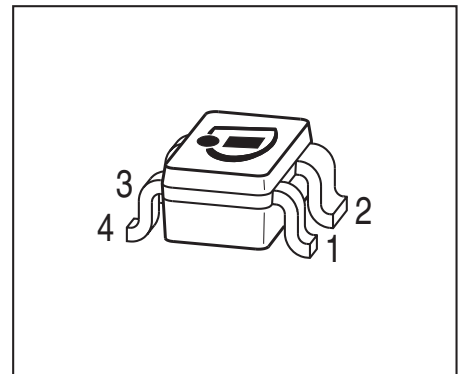


Silicon N-Channel MOSFET Tetrode

- Low noise gain controlled input stages of UHF- and VHF - tuners with 3 V up to 5 V supply voltage
- Integrated gate protection diodes
- Excellent noise figure
- High gain, high forward transadmittance
- Improved cross modulation at gain reduction
- Pb-free (RoHS compliant) package
- Qualified according AEC Q101



ESD (Electrostatic discharge) sensitive device, observe handling precaution!

Type	Package	Pin Configuration						Marking
BF5020	SOT143	1 = S	2 = D	3 = G2	4 = G1	-	-	KYs
BF5020R	SOT143R	1 = D	2 = S	3 = G1	4 = G2	-	-	KYs
BF5020W	SOT343	1 = D	2 = S	3 = G1	4 = G2	-	-	KYs

Maximum Ratings

Parameter	Symbol	Value	Unit
Drain-source voltage	V_{DS}	8	V
Continuous drain current	I_D	25	mA
Gate 1/ gate 2-source current	I_{G1S}, I_{G2S}	± 10	mA
Gate 1/ gate 2-source voltage	V_{G1S}, V_{G2S}	± 6	V
Total power dissipation	P_{tot}		mW
$T_S \leq 76^\circ\text{C}$, BF5020, BF5020R		200	
$T_S \leq 94^\circ\text{C}$, BF5020W		200	
Storage temperature	T_{stg}	-55 ... 150	$^\circ\text{C}$
Channel temperature	T_{ch}	150	

Thermal Resistance

Parameter	Symbol	Value	Unit
Channel - soldering point ¹⁾ BF5020, BF5020R BF5020W	R_{thchs}	≤ 370 ≤ 280	K/W

Electrical Characteristics at $T_A = 25^\circ\text{C}$, unless otherwise specified

Parameter	Symbol	Values			Unit
		min.	typ.	max.	
DC Characteristics					
Drain-source breakdown voltage $I_D = 20\text{ }\mu\text{A}$, $V_{G1S} = 0$, $V_{G2S} = 0$	$V_{(BR)DS}$	12	-	-	V
Gate1-source breakdown voltage $+I_{G1S} = 10\text{ mA}$, $V_{G2S} = 0$, $V_{DS} = 0$	$+V_{(BR)G1SS}$	6	-	15	
Gate2-source breakdown voltage $+I_{G2S} = 10\text{ mA}$, $V_{G1S} = 0$, $V_{DS} = 0$	$+V_{(BR)G2SS}$	6	-	15	
Gate1-source leakage current $V_{G1S} = 6\text{ V}$, $V_{G2S} = 0$, $V_{DS} = 0$	$+I_{G1SS}$	-	-	50	nA
Gate2-source leakage current $V_{G2S} = 6\text{ V}$, $V_{G1S} = 0$, $V_{DS} = 0$	$+I_{G2SS}$	-	-	50	
Drain current $V_{DS} = 5\text{ V}$, $V_{G1S} = 0$, $V_{G2S} = 4\text{ V}$	I_{DSS}	-	-	100	
Drain-source current $V_{DS} = 5\text{ V}$, $V_{G2S} = 4\text{ V}$, $R_{G1} = 120\text{ k}\Omega$	I_{DSX}	-	14	-	mA
Gate1-source pinch-off voltage $V_{DS} = 5\text{ V}$, $V_{G2S} = 4\text{ V}$, $I_D = 20\text{ }\mu\text{A}$	$V_{G1S(p)}$	-	0.7	-	V
Gate2-source pinch-off voltage $V_{DS} = 5\text{ V}$, $I_D = 20\text{ }\mu\text{A}$, $V_{G1S} = 2\text{ V}$	$V_{G2S(p)}$	-	0.7	-	

¹⁾For calculation of R_{thJA} please refer to Application Note Thermal Resistance

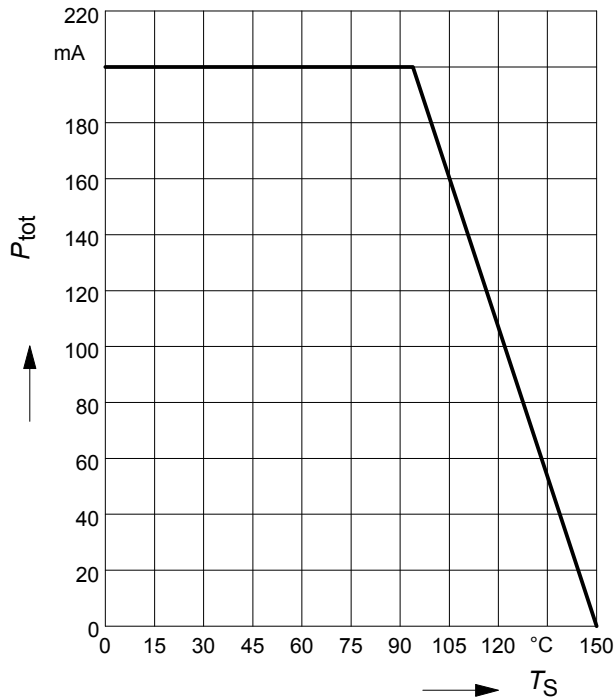
Electrical Characteristics at $T_A = 25^\circ\text{C}$, unless otherwise specified

Parameter	Symbol	Values			Unit
		min.	typ.	max.	
AC Characteristics - (verified by random sampling)					
Forward transconductance $V_{DS} = 5\text{ V}$, $I_D = 10\text{ mA}$, $V_{G2S} = 4\text{ V}$	g_{fs}	-	34	-	mS
Gate1 input capacitance $V_{DS} = 5\text{ V}$, $I_D = 10\text{ mA}$, $V_{G2S} = 4\text{ V}$	C_{g1ss}	-	2.4	-	pF
Output capacitance $V_{DS} = 5\text{ V}$, $I_D = 10\text{ mA}$, $V_{G2S} = 4\text{ V}$	C_{dss}	-	1	-	
Power gain $V_{DS} = 5\text{ V}$, $I_D = 10\text{ mA}$, $V_{G2S} = 4\text{ V}$, $f = 800\text{ MHz}$ $V_{DS} = 5\text{ V}$, $I_D = 10\text{ mA}$, $V_{G2S} = 4\text{ V}$, $f = 45\text{ MHz}$	G_p	-	26	-	dB
		-	32	-	
Noise figure $V_{DS} = 5\text{ V}$, $I_D = 10\text{ mA}$, $V_{G2S} = 4\text{ V}$, $f = 800\text{ MHz}$ $V_{DS} = 5\text{ V}$, $I_D = 10\text{ mA}$, $V_{G2S} = 4\text{ V}$, $f = 45\text{ MHz}$	F	-	1.2	-	dB
		-	0.8	-	
Gain control range $V_{DS} = 5\text{ V}$, $V_{G2S} = 4...0\text{ V}$	ΔG_p	-	45	-	
Cross-modulation ¹⁾ , $V_{DS} = 5\text{ V}$, $R_{G1} = 120\text{ k}\Omega$ $AGC = 0$ $AGC = 10\text{ dB}$ $AGC = 40\text{ dB}$	X_{mod}	-	98	-	dBμV
		-	96	-	
		-	106	-	

¹⁾Input level for $k = 1\%$; $f_w = 50\text{ MHz}$, $f_{unw} = 60\text{ MHz}$

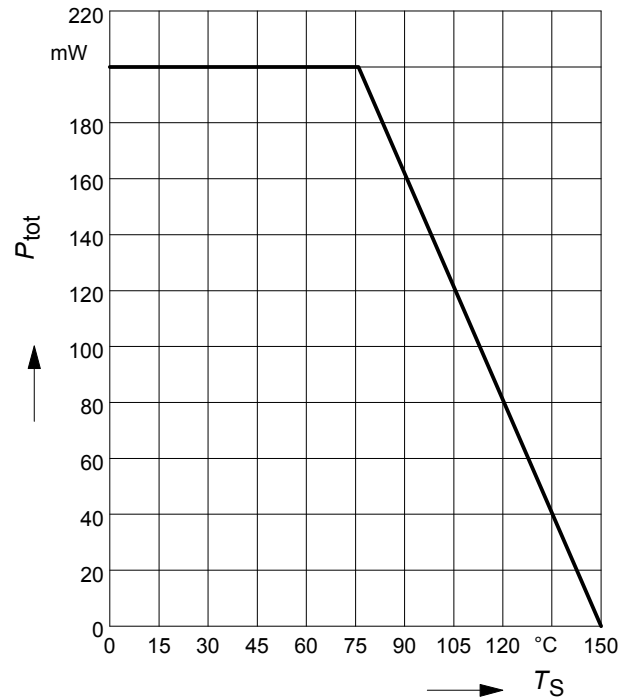
Total power dissipation $P_{\text{tot}} = f(T_S)$

BF5020W

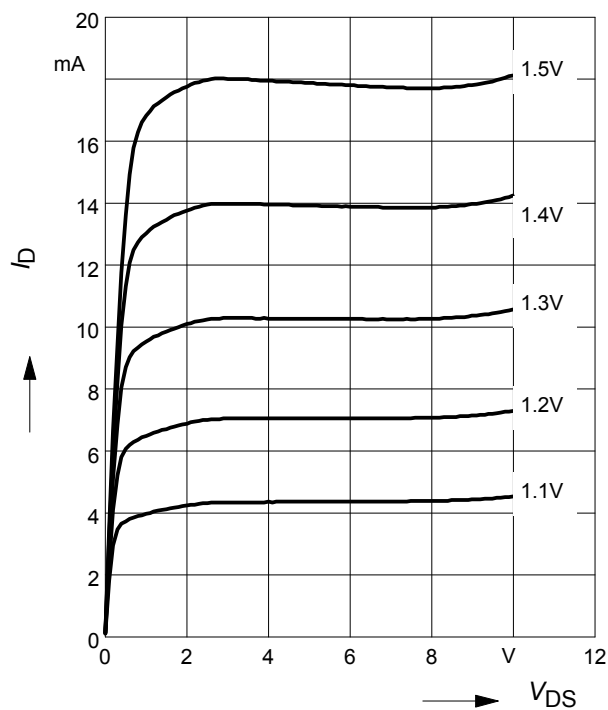


Total power dissipation $P_{\text{tot}} = f(T_S)$

BF5020, BF5020R



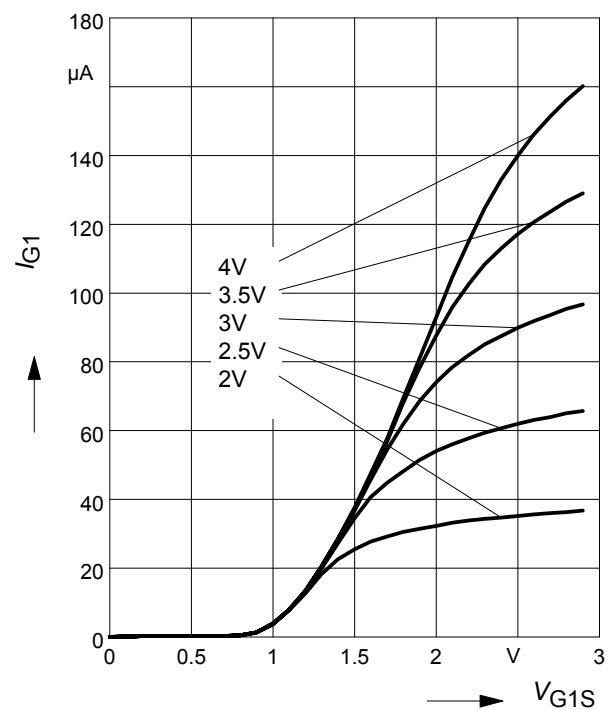
Output characteristics $I_D = f(V_{\text{DS}})$



Gate 1 current $I_{\text{G1}} = f(V_{\text{G1S}})$

$V_{\text{DS}} = 5\text{V}$

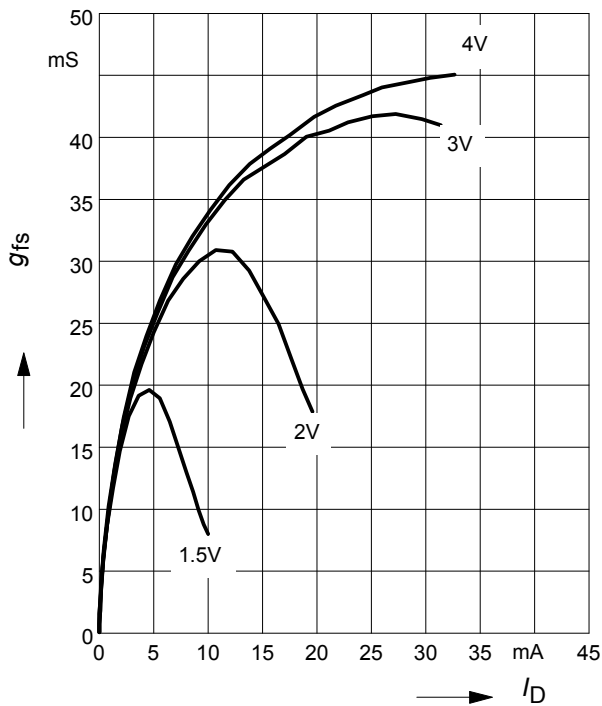
$V_{\text{G2S}} = \text{Parameter}$



Gate 1 forward transconductance

$$g_{fs} = f(I_D)$$

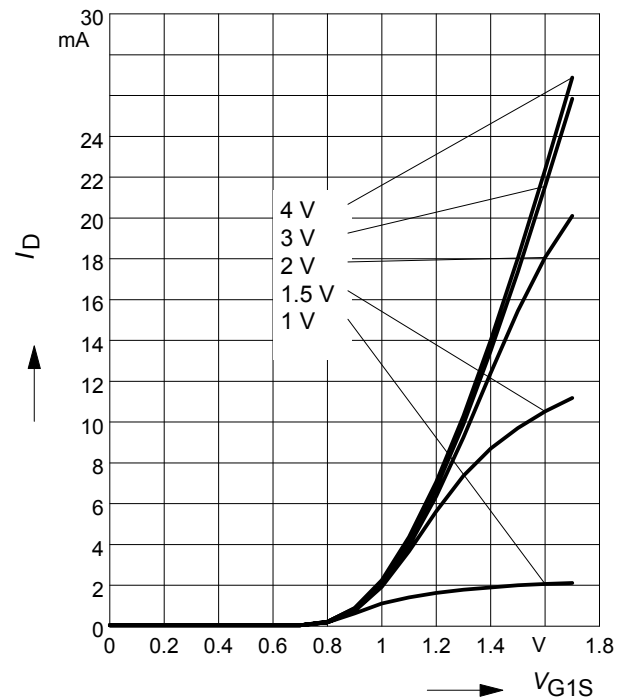
$V_{DS} = 5V$, $V_{G2S} = \text{Parameter}$



Drain current $I_D = f(V_{G1S})$

$V_{DS} = 5V$

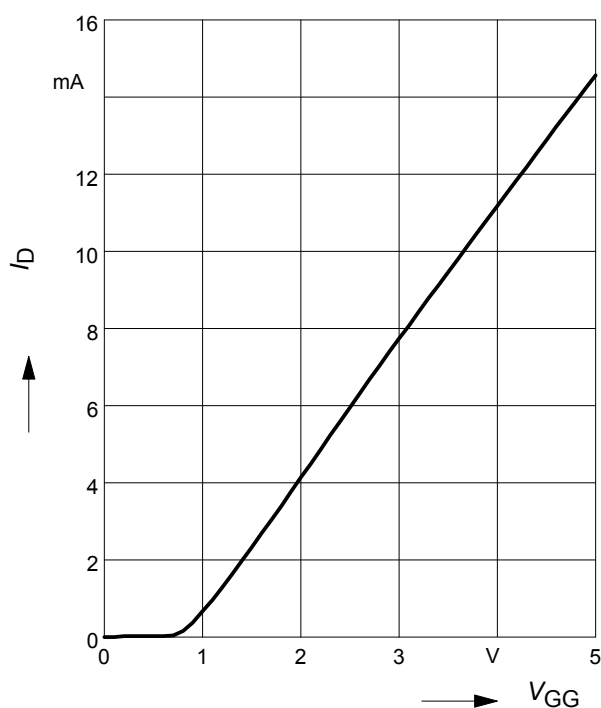
$V_{G2S} = \text{Parameter}$



Drain current $I_D = f(V_{GG})$

$V_{DS} = 5V$, $V_{G2S} = 4V$, $R_{G1} = 120\text{ k}\Omega$

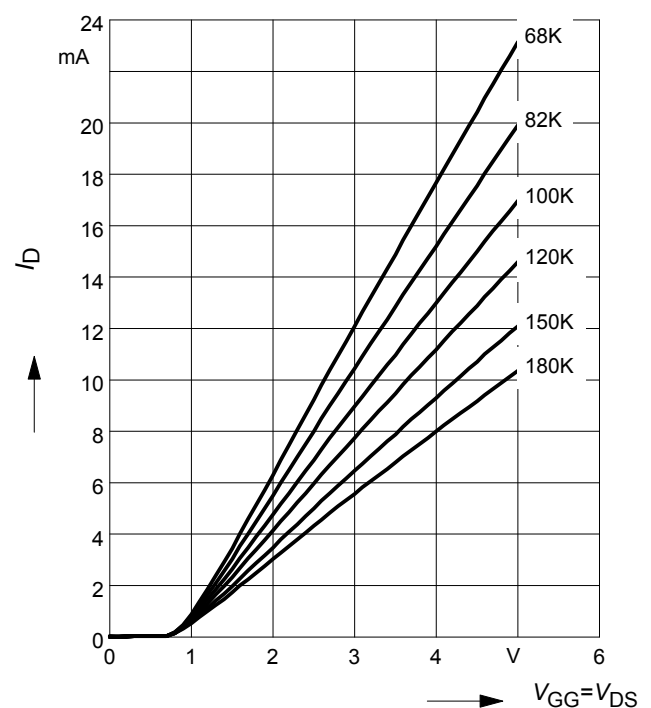
(connected to V_{GG} , $V_{GG} = \text{gate1 supply voltage}$)



Drain current $I_D = f(V_{GG})$

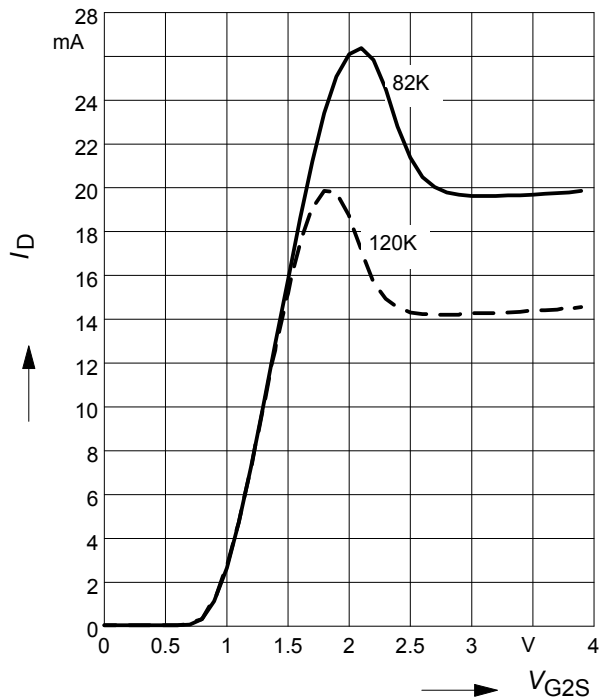
$V_{G2S} = 4V$

$R_{G1} = \text{Parameter in k}\Omega$



Drain current $I_D = f(V_{G2S})$

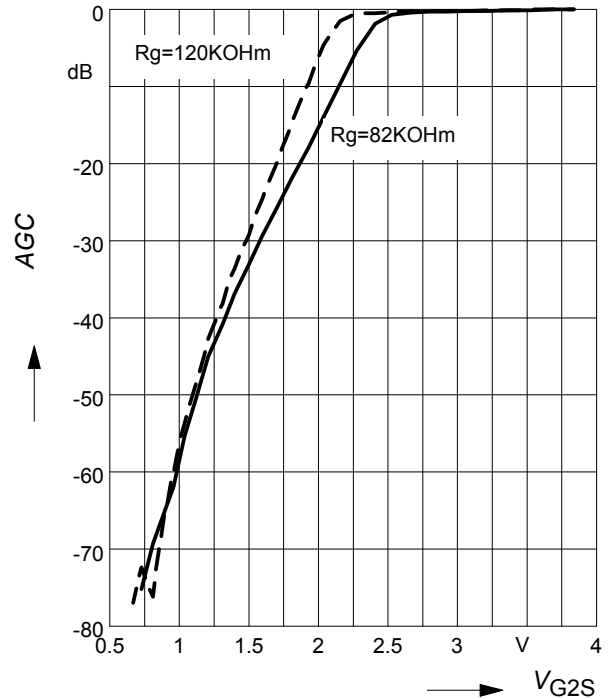
$V_{DS} = 5\text{ V}$, $R_{G1} = \text{Parameter in k}\Omega$



AGC characteristic $AGC = f(V_{G2S})$

$f = 50\text{ MHz}$

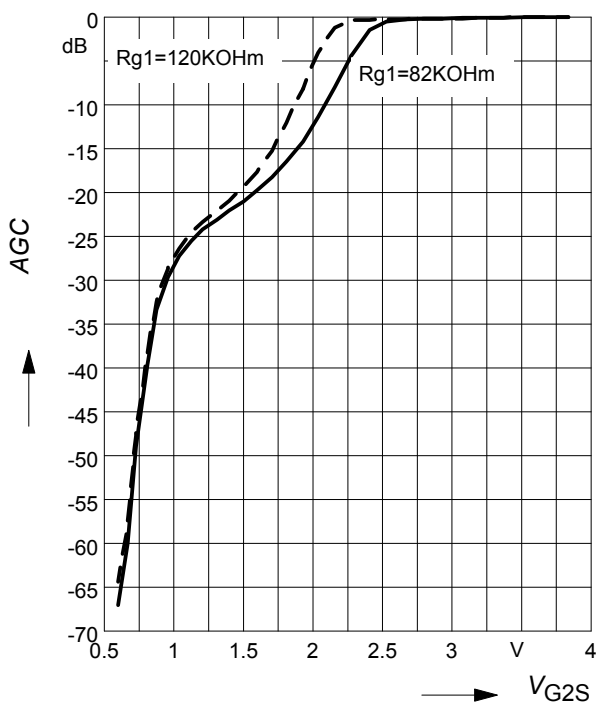
measured in test circuit, see page 7



AGC characteristic $AGC = f(V_{G2S})$

$f = 800\text{ MHz}$

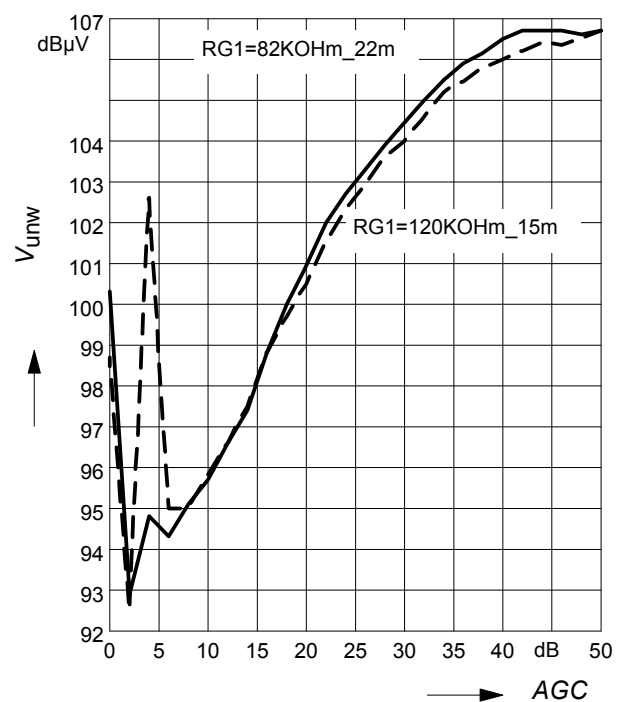
measured in test circuit, see page 7



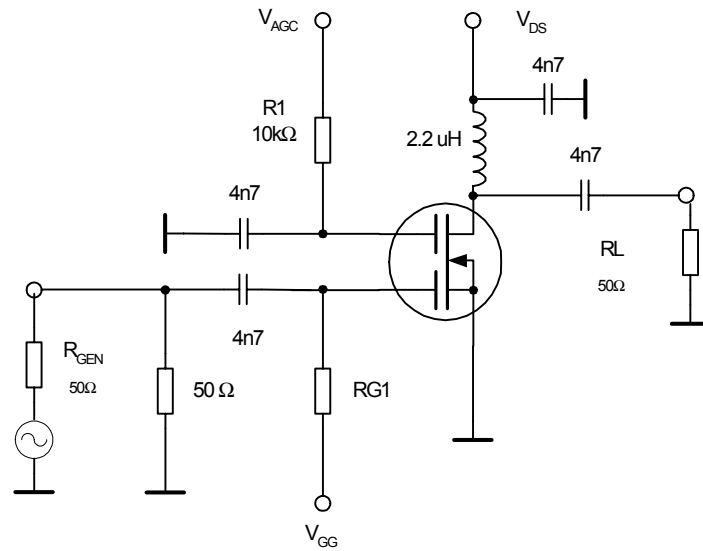
Crossmodulation $V_{unw} = (AGC)$

$V_{DS} = 5\text{ V}$

measured in test circuit, see page 7

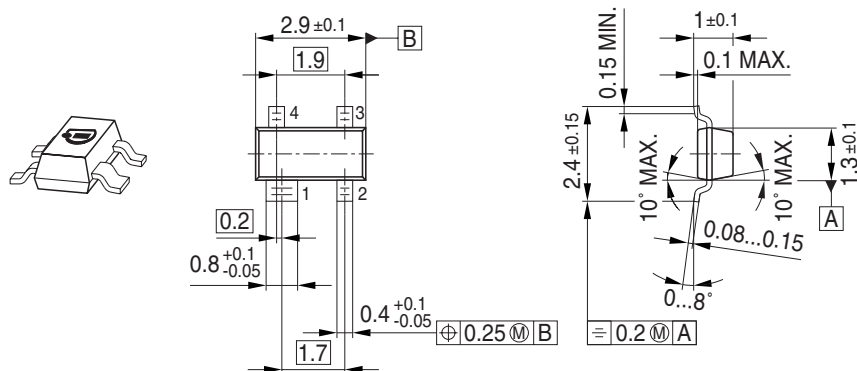


Test circuit for Crossmodulation / AGC

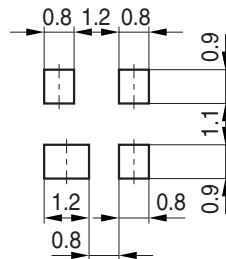


Semibiased

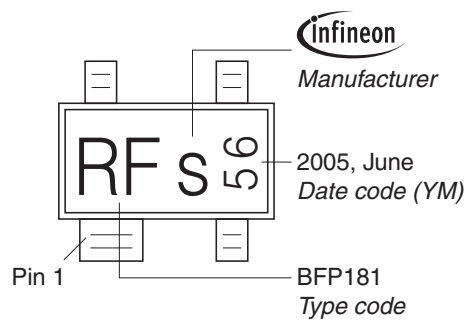
Package Outline



Foot Print

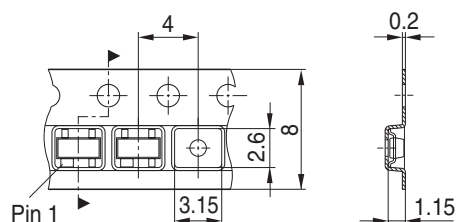


Marking Layout (Example)



Standard Packing

Reel ø180 mm = 3.000 Pieces/Reel
 Reel ø330 mm = 10.000 Pieces/Reel



Reverse bar

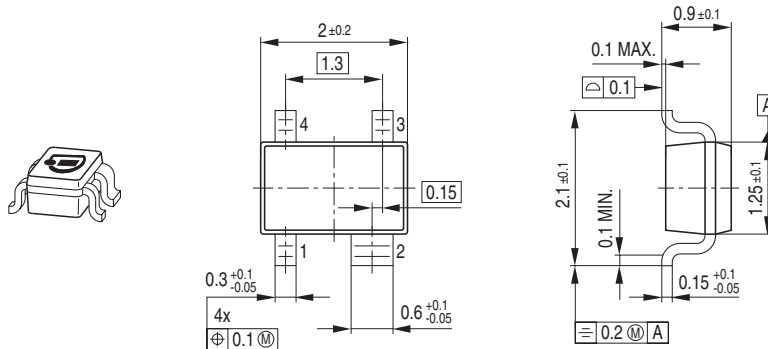
2005, June
Date code (YM)

infineon
Manufacturer

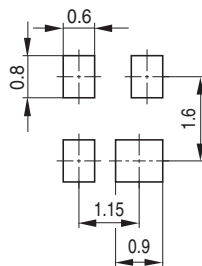
BFP181R
Type code

Pin 1

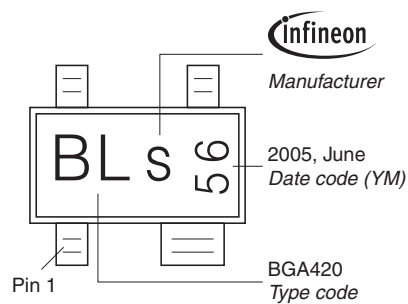
Package Outline



Foot Print

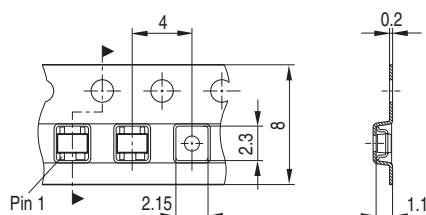


Marking Layout (Example)



Standard Packing

Reel $\phi 180 \text{ mm}$ = 3.000 Pieces/Reel
 Reel $\phi 330 \text{ mm}$ = 10.000 Pieces/Reel



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